Sheet 1 of 1

FORM PTO-1449

## U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMORE GENICE

ATTY. DOCKET NO.

SERIAL NO.

PKHF-05004US

APPLICANT

10/589,852

LIST OF REFERENCES CITED BY APPLICANT 0 2008

(Use several sheets if necessary)

Noboru ICHINOSE

FILING DATE

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/D.W./	AG	2002-093243	03/29/2002	JAPAN (See U.S. 6,897,56	JAPAN (See U.S. 6,897,560)				T	ABE
/D.W./	AH	2004-056098	02/19/2004	JAPAN (See U.S. 7,319,249 and U.S. 6,977,397)					,	ABE
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/D.W./	AK	OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)  Harwig et al., "Electrical Properties of b-Ga2O3 Single Crystals. II," Journal of Solid State Chemistry Vol. 23, pages 205-211, 15 January 1978. (Previously Submitted)								
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	AO	Harwig, T. et al., "Electrical Properties of B-Ga2O3 Single Crystals. II", In: Journal of Solid State Chemistry, 15 January, 1978 (15.01.78), Vol. 23, pages 205 to 211. (Previously Submitted)								
V	AP	Japanese Office Action dated August 5, 2008 with Partial English Translation								
EXAMINER		/Daniel Whalen/	í	DATE CONS	IDERED					

'EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

01/28/2009